

HIGH-PERFORMANCE-SENSORSYSTEME durch Verbindung von Siliziumtechnologie und keramischer Mehrlagentechnik

HIPS | HIGH PERFORMANCE SENSORS

Powered by SiCer - The best of both worlds

IVAM Midweek Coffee Break
Overview Part 1 HIPS Joint Research Project:

SiCer Technology Platform for Complex Sensors

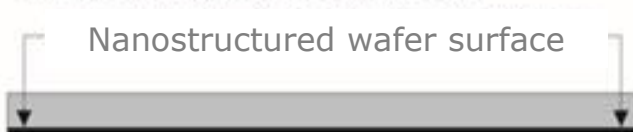
Franz Bechtold e.a.

- **Technology platform**
- **Current approach, partners**
- **Milestones on the road to success**
- **Milestone 1 and 2 results**
- **Highlights from the consortium**
- **Milestone 3 achievements**
- **Summary and conclusion**

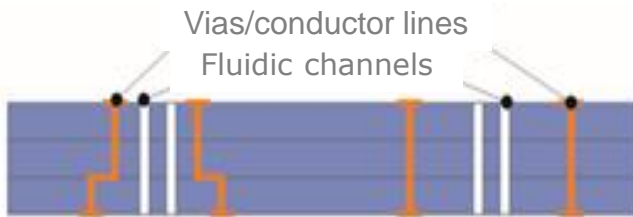
A silicon-LTCC composite substrate with special properties

The SiCer composite substrate is fabricated by sintering LTCC film onto a silicon wafer at 900°C.

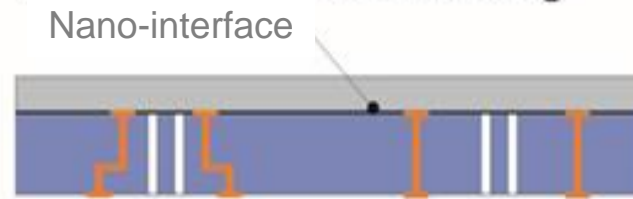
1. Etching the Si wafer



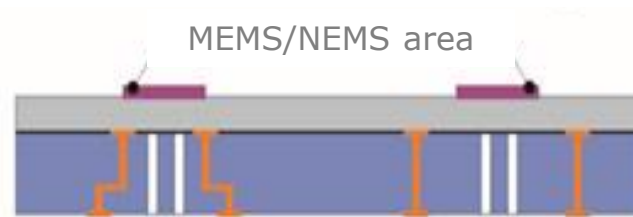
2. LTCC processing (green)



3. Lamination & Sintering



4. Thin-film processing



5. Separation by Si etching

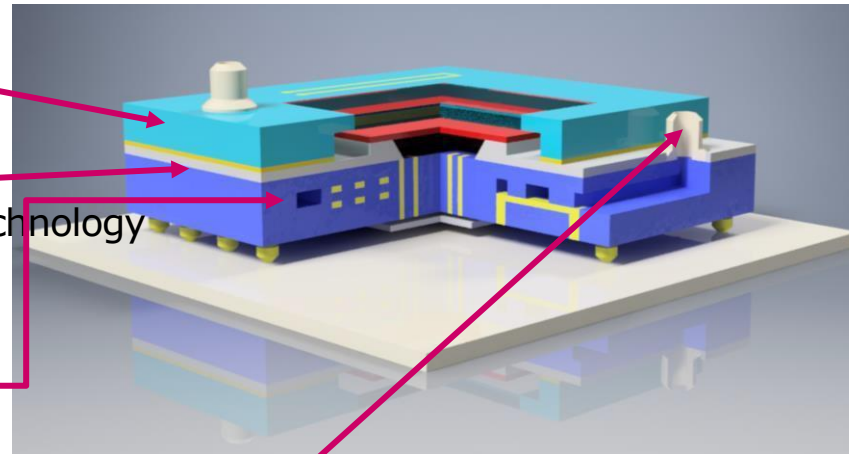


6. Packaging & Singulation



Illustration of the SiCer technology platform elements

- Topic 1: Materials
 - Eg. Glassceramics, Metallization, Functional layers
- Topic 2: Processes
 - Eg. Sintering, Assembly and Packaging technology
- Topic 3.1 Structures
 - Eg. Membrane, Channel
- Topic 3.2: Features
 - Eg. Reaction chamber, Fluidic Interface



Partner
Fraunhofer IKTS (IKTS)
Technical University Ilmenau (TUIL)
University of applied science – Jena (EAH)
Micro-Hybrid Electronic GmbH (MHE)
VIA electronic GmbH (VIA)
IMMS GmbH (MMS)
CIS Forschungsinstitut (CIS)
5 microns GmbH (5M)
Siebert TFT GmbH (STFT)
Abatec Mikrosysteme GmbH (former LHT)
LLT Applikation GmbH (LLT)

1. Process capability of the material system

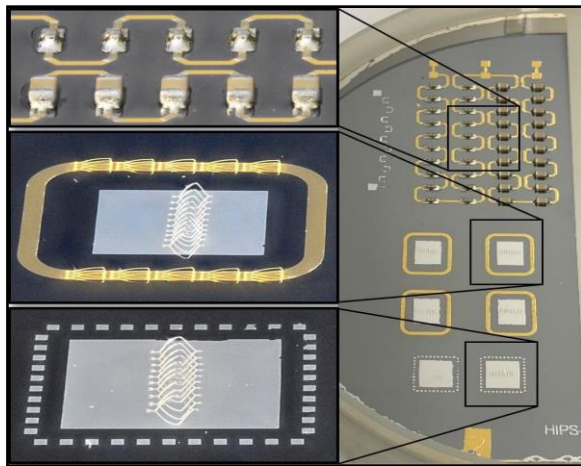
- 1st generation tape with a thickness of $100 - 120\mu\text{m} \pm 10\%$ and sheet size of 4 "x4" is useable
- Compatibility of the commercial pastes for the basic processes are validated and is available
- Bonding of Si and Ceramic with low pressure assisted sintering is developed and validated
- SiCer basic process is feasible and validated at the partners' sites

2. System capability

- Interfaces for bonding and soldering processes are available
- Design rules for the Assembly and packaging technologies are available
- Bonding and soldering processes can be performed and are validated

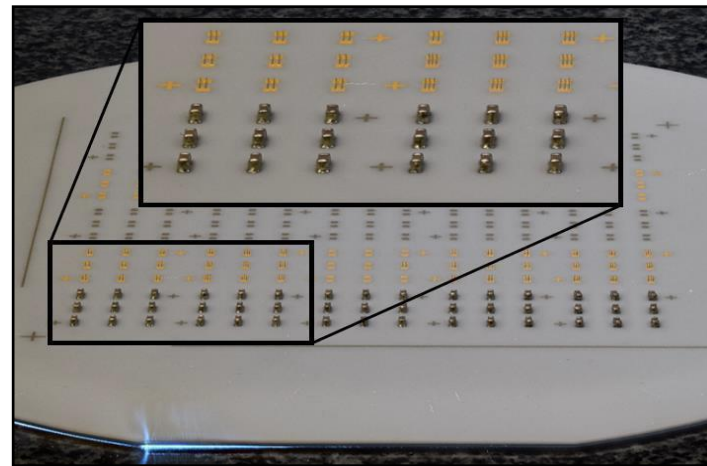
Assembly and packaging technology (AVT):

- Interface for the bonding and soldering are validated both on Si and LTCC side.
- Components have been successfully soldered and wire bonded in their respective soldering and wire bonding areas both on Si side and LTCC side.



Silicon side

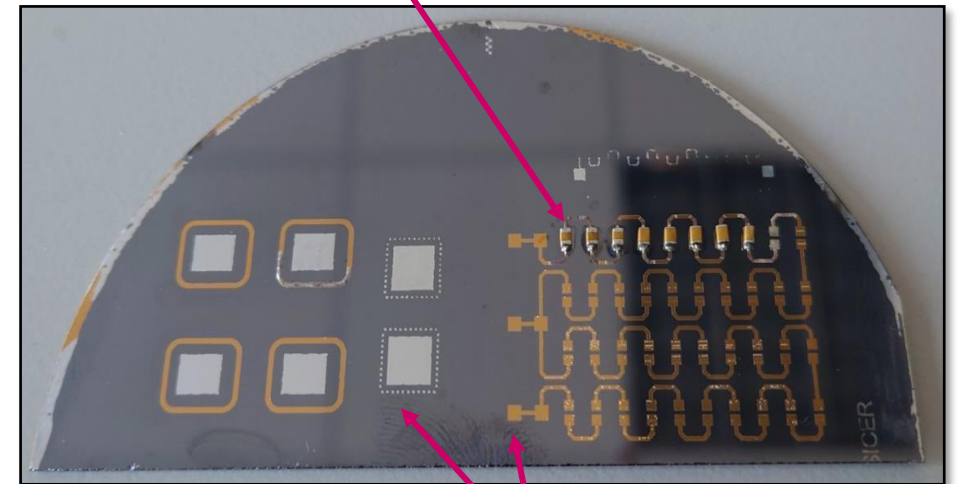
Sample Id: CK13_MS2_2



Ceramic side

Sample Id: CK13_MS2_9

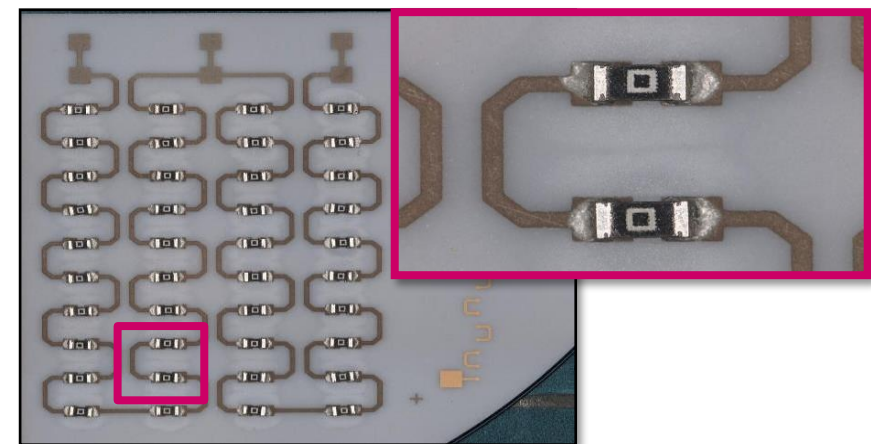
Soldering interface – Si side



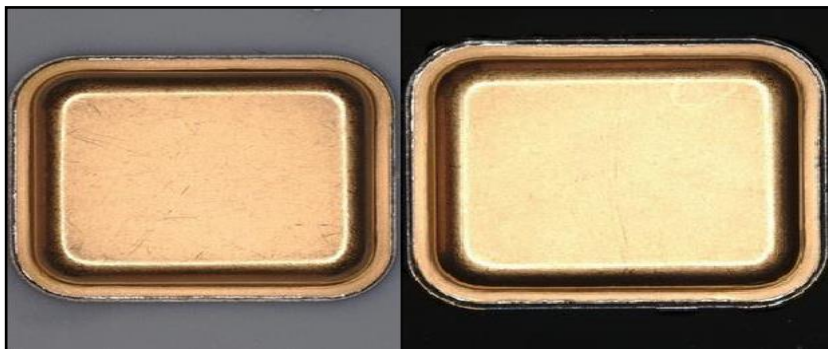
Bonding interface – Si side

Evaluated at 4 different partners: LHT, CIS, TUIL, MHE

Assembly characterisation :



Daisy-chain structures with soldered SMD components



Vacuum-brazed Kovar caps: Left –Ceramic side; Right: Si side

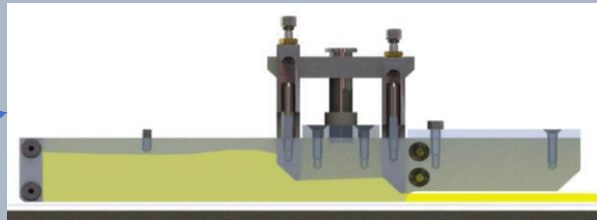
Climate test - SiCer					
AVT	Substrates soldered LTCC side		Substrate Wire bonded (Alu 32 µm)	Substrates with hermeticity	
Material	Almit LFM48U MDA-5 (Jetter)	Koki SnAg3Cu7	Ceramic side	Kovar cap on Ceramic side	Kovar cap on Si side
Thermal shock test (-40 ... +85°C; 100 cycles; Dwell time 30 min, Transition time 10s)	No abnormalities visible	No abnormalities visible	No abnormalities visible	-	No abnormali ties
Climate storage test (100,500,1000h at +85°C)	100h without abnormalities	100h without abnormalities	Upto 100h without abnormalities	-	-
Humidity storage test (85% humidity, 85°C, 168h)	Test in progress		Test in progress	Test in progress	

Progress in the main topics

- **Material development:** Tape, pastes, functional materials
- **Process optimization:** Pretreatment, laminating, cofiring, release tapes, sacrificial materials
- **Structural and demonstrator elements:** Cavities and channels
- **Integration of sensor and electrical functions:** electrostatic toolbox. NTC resistors
- **Process upscaling:** Tape casting, sheet size

Upscaling:

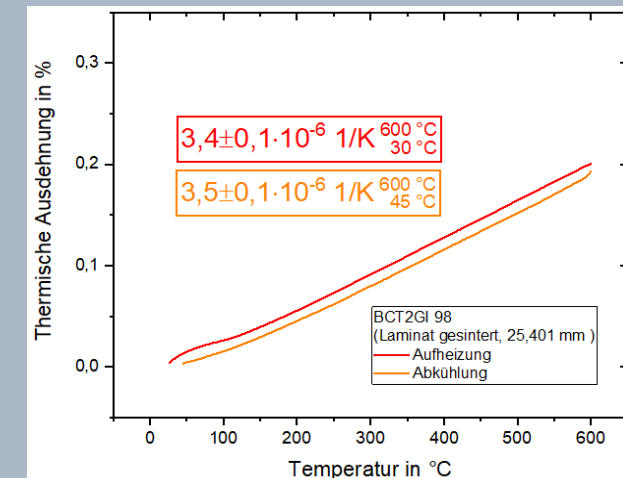
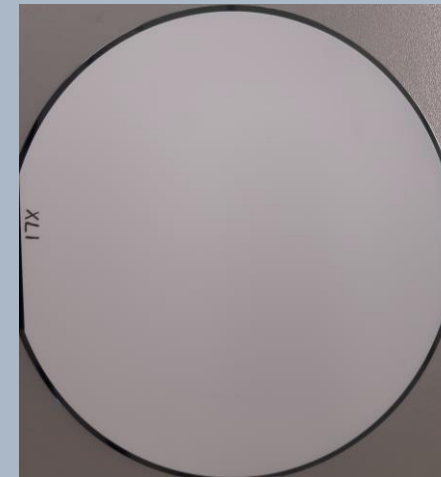
- Development of continuous tape casting process to produce larger quantity of tape
- From the laboratory to the pilot production scale
- Adjustment of the casting parameters
 - Squeegee gap, casting speed, Casting box width
 - Temperature profile in the drying channel

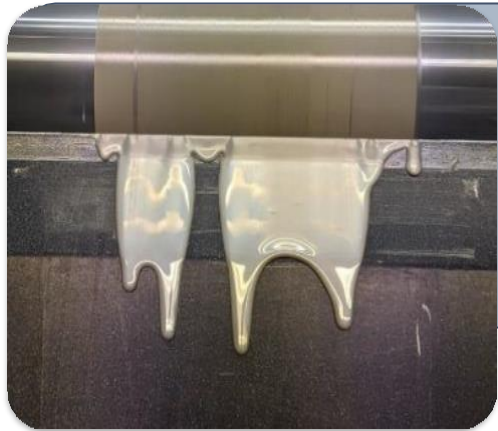


Further development of the LTCC recipe

Adaptation of the CTE

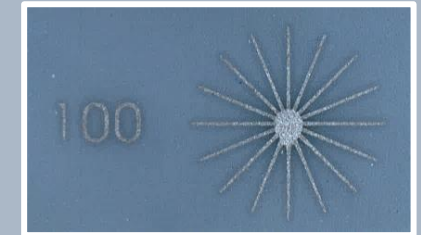
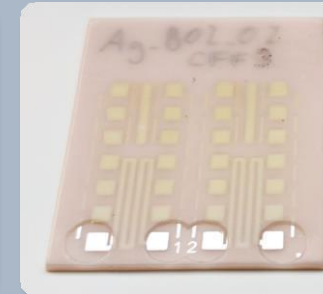
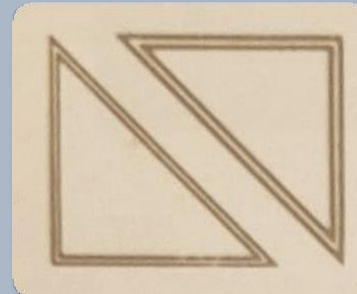
- Casting the new film composition
- Test of the new film composition
- Coefficient of Expansion
 - Shrinkage
 - Density
 - Behaviour in SiCer-Process





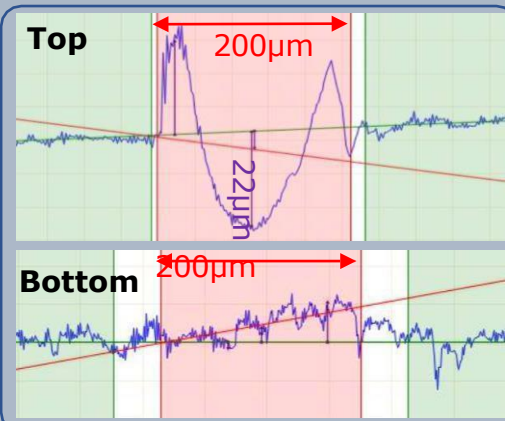
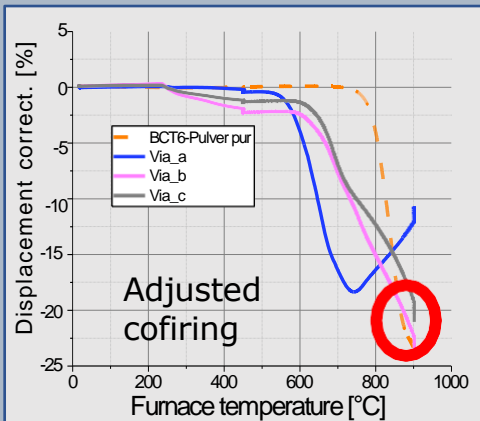
- Paste: Preparation and characterization
- Application dependent optimization

Conductor prints



- Ag-based metallization for buried structures available
- Necessary print resolution achieved

Viafill



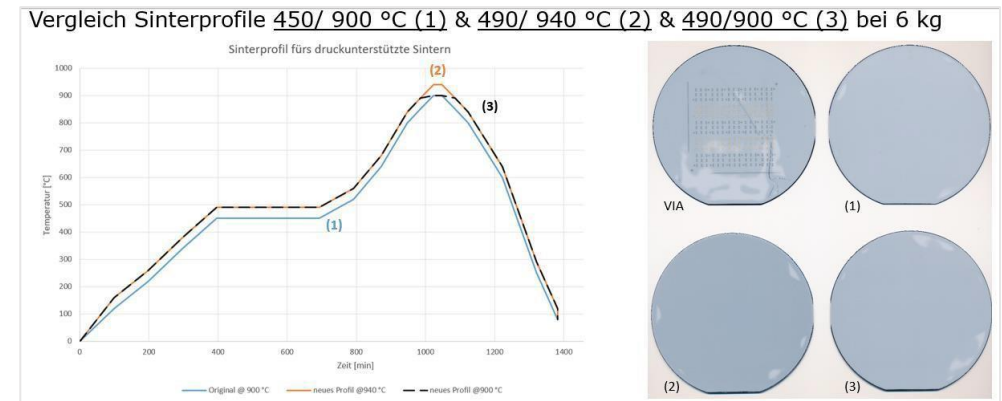
- Shrinkage matched to BCT6
- Processability confirmed
- Filling of 100 µm-Vias for 250 µm tape thickness possible

Further metal paste developments

- Transition-paste for mixed metal system (Au-Ag)
- Ag-Pd-Pt-solderable paste
- Polymer paste for Through-Silicon-Via Technology

Systematic investigation of sinterparameter

- Adjusted burnout- & sintering temperature for pressure assisted sintering (6 kg – fixed weight)
- Profile (2) shows best results followed by profile (3)
- Pulltest to characterize bond interface

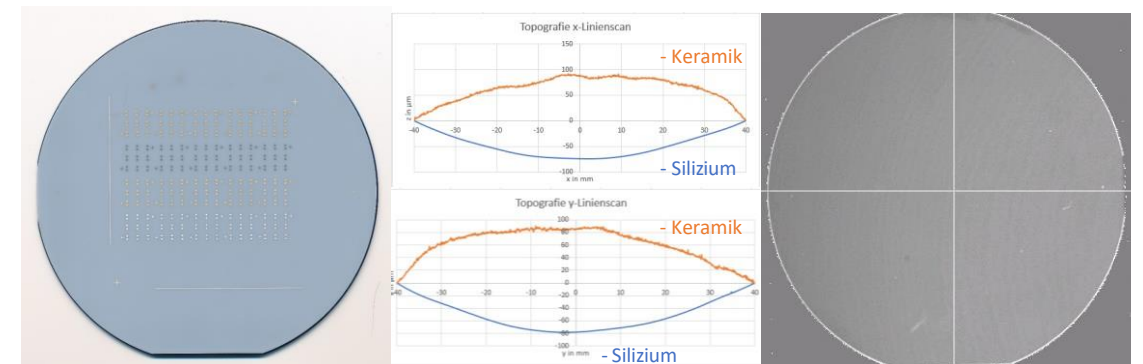


Influence of burnout & sintering temperature on the bond interface of BCT6 H066

Investigation of metallization and release tape interaction

- Combination of 4 release tapes and 4 metallization pastes (BCT6 H100)
- Releasetapes: IKTS F800, IKTS F1000, CeramTecA, Kerafol
- Pastes: QR 150¹, LL 509¹, 5740 A¹, 7454 B²

¹ DuPont, ² Namics



Bow-measurement and US-microscopy in SiCer

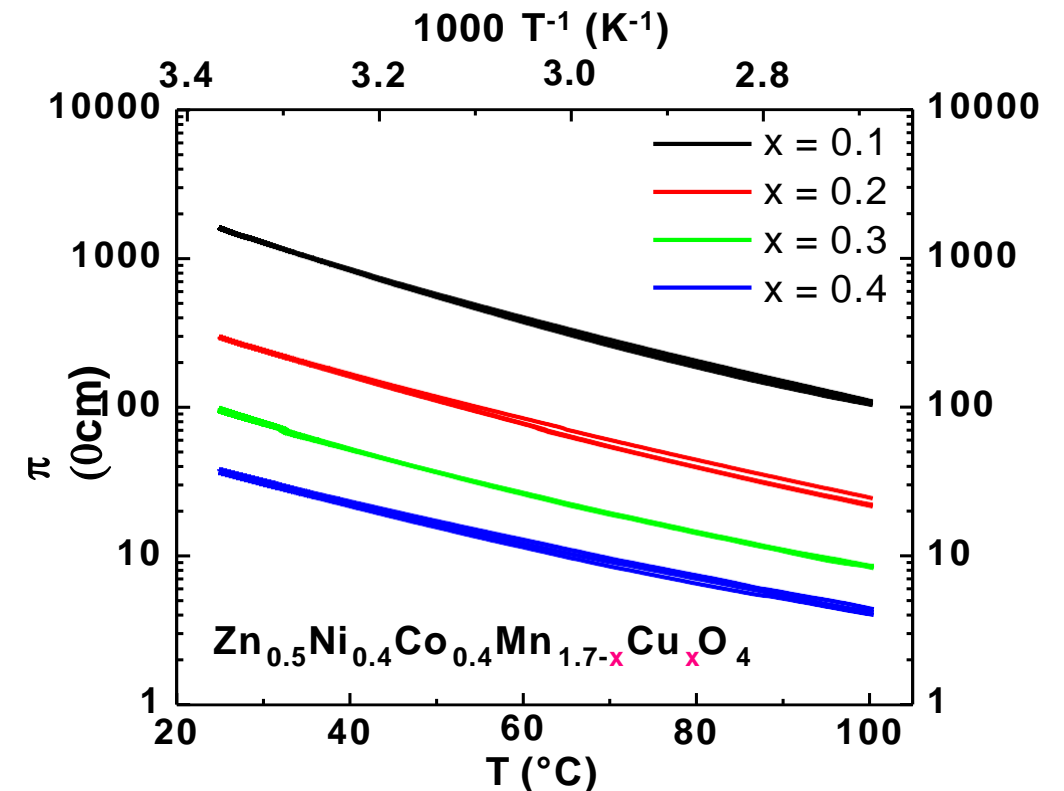
Developed within HIPS

Functional materials

- Magnetic shielding: $\text{Ni}_{0.5}\text{Zn}_{0.5}\text{Fe}_2\text{O}_4 + 3 \text{ Ma.-% Bi}_2\text{O}_3$
- Inductive components: $\text{Ni}_{0.3}\text{Cu}_{0.2}\text{Zn}_{0.52}\text{Fe}_{1.98}\text{O}_{3.99}$
- Capacitor material: $\frac{1}{2}\text{TiO} + 1 \text{ Ma.-% CuO}$
- NTC resistor: $\text{Zn}_{0.5}\text{Ni}_{0.4}\text{Co}_{0.4}\text{Mn}_{1.3}\text{Cu}_{0.4}\text{O}_4$

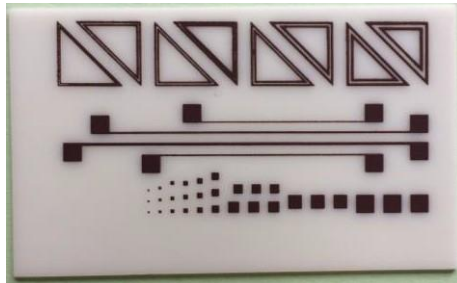
Paste composition

- Solid content: $\approx 70 \text{ Ma.-%}$
- Organics: $\approx 30 \text{ Ma.-%}$

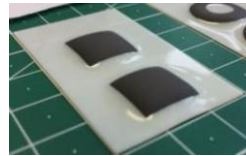


IKTS & EAH test structures

Funktion: 1.4.2 magn. shielding

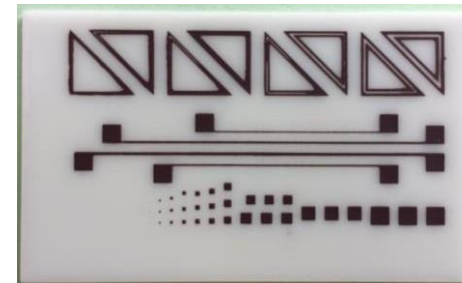


Postfiring

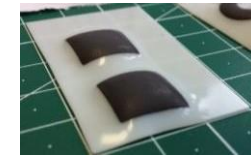


Cofiring

Funktion: 1.4.3 inductive components

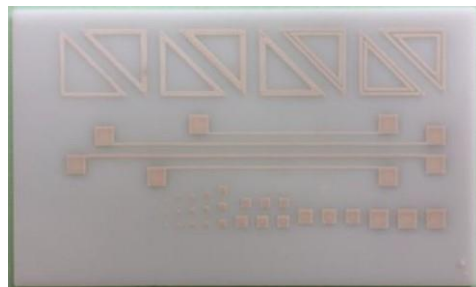


Postfiring



Cofiring

Funktion: 1.4.4 capacitor material

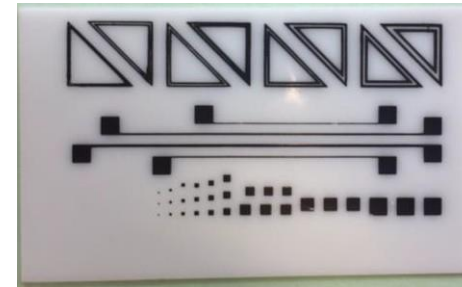


Postfiring

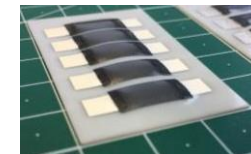


Cofiring with Ag-conductor (IKTS)

Funktion: 1.4.5 NTC resistors



Postfiring

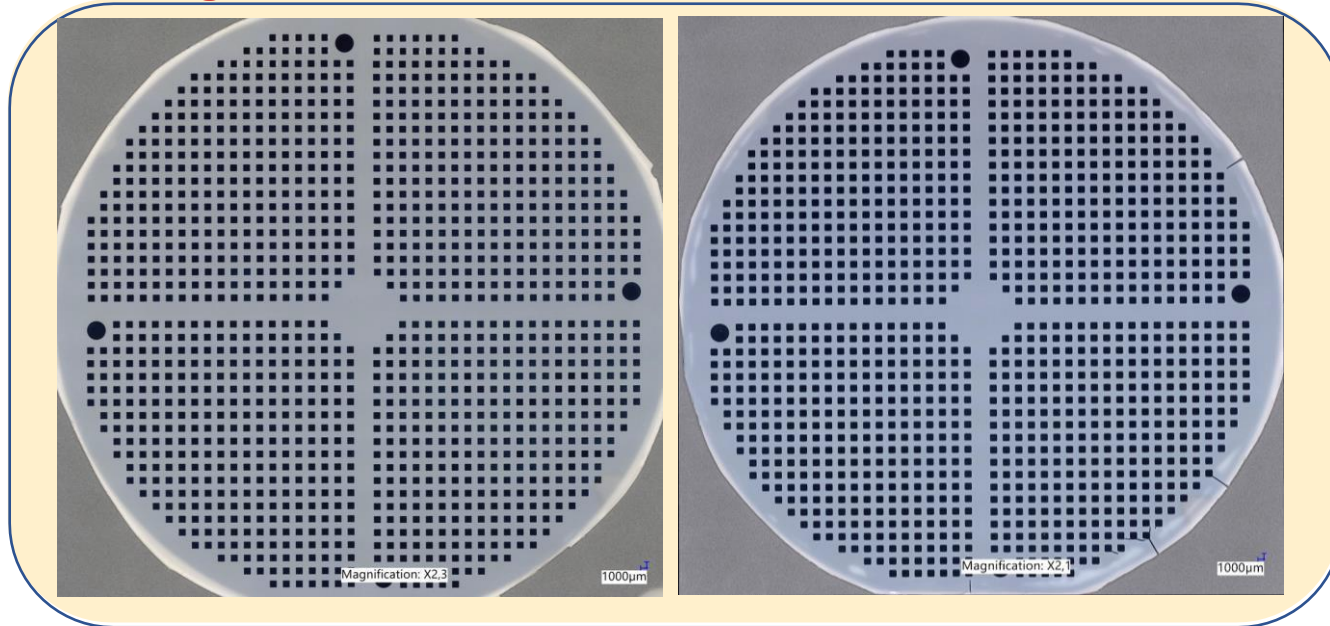


Cofiring with Ag-conductor (IKTS)

SiCer tests with open cavities in LTCC

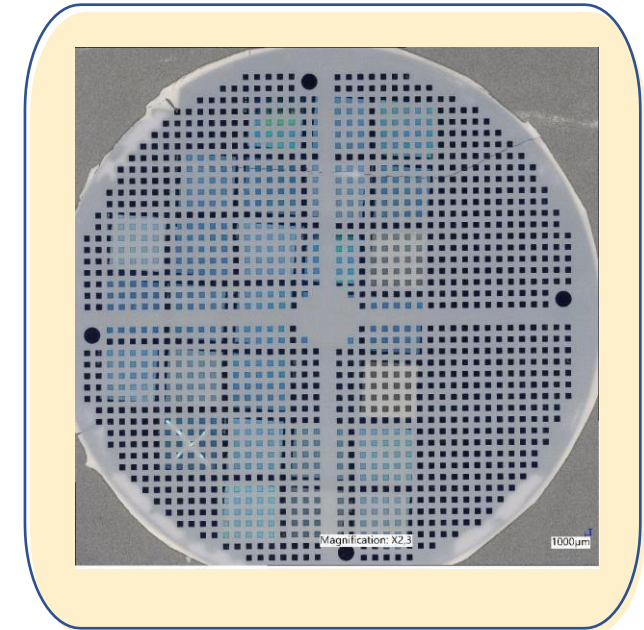
11.5 kg

No weight

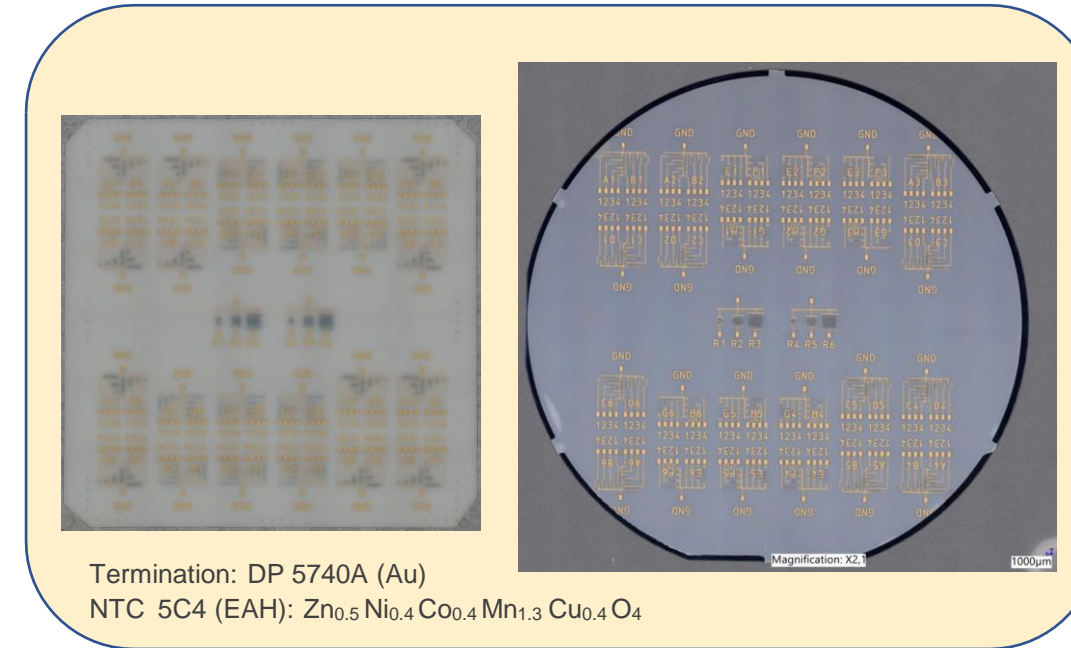
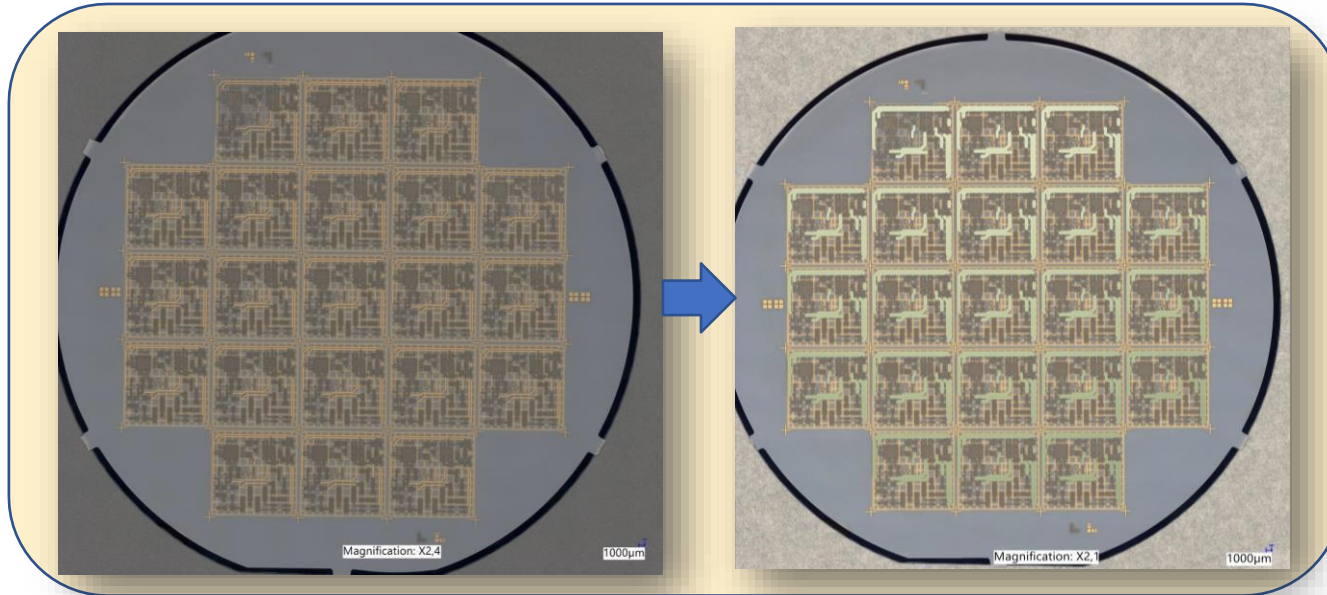


- Crack-free SiCer with open cavities, 2DT
- Very good and uniform bonding
- IR sensor design 1.1 mm x 1.1 mm

Investigation of different Si-LTCC interfaces by laser surface activation

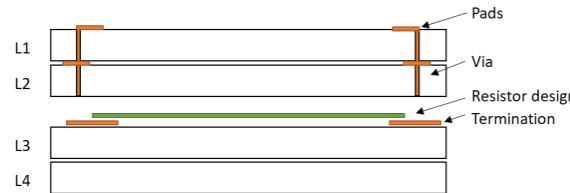


- Areas with better bonding behaviour were chosen for lasering of full wafer by LLT



- 2 Double tapes
- Contact-pads (Au DP5740)
- Vias (Au DP5738R)
- Inner metallization (Au DP5740)
- Outer signal lines (Au DP5740)
- Outer solder pads (AuPt LL509)

Postfired glass as solder stop

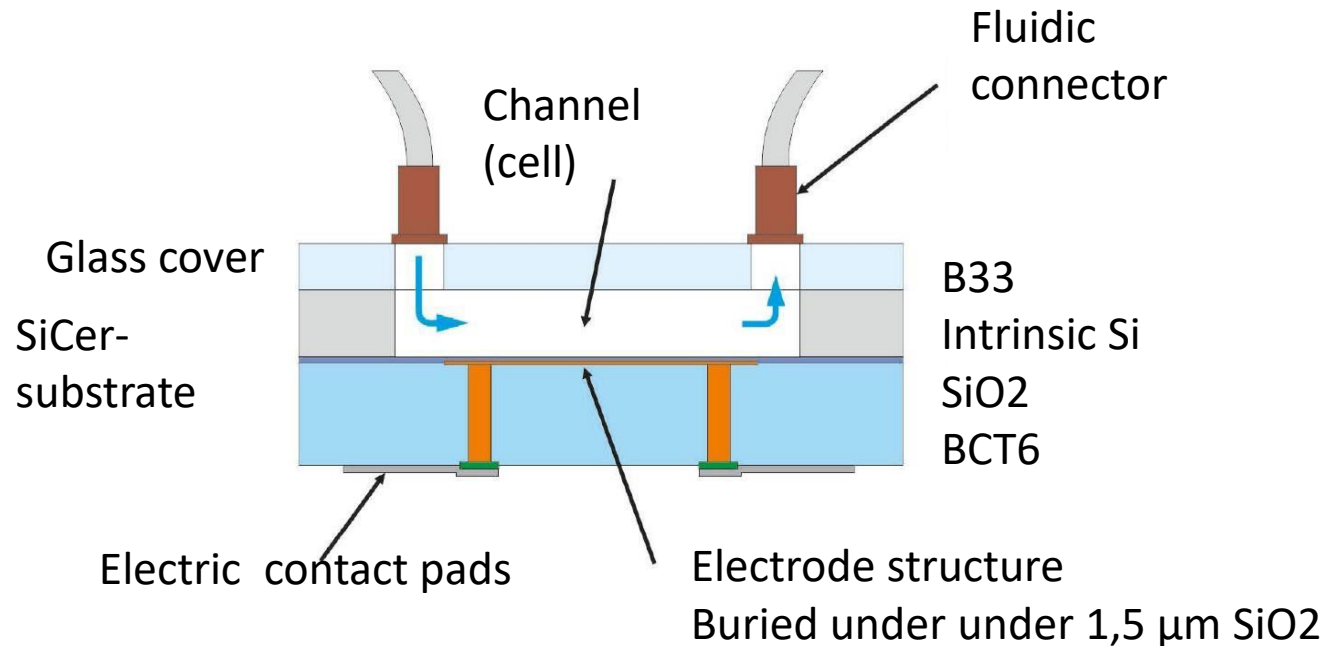


Evaluation of NTC paste (from EAH) for T-sensors

- Constrained sintering,
- 2 DT 11.4 kg
- No crack or warpage
- SiCer,
- 2 DT 11.4 kg
- No crack or warpage

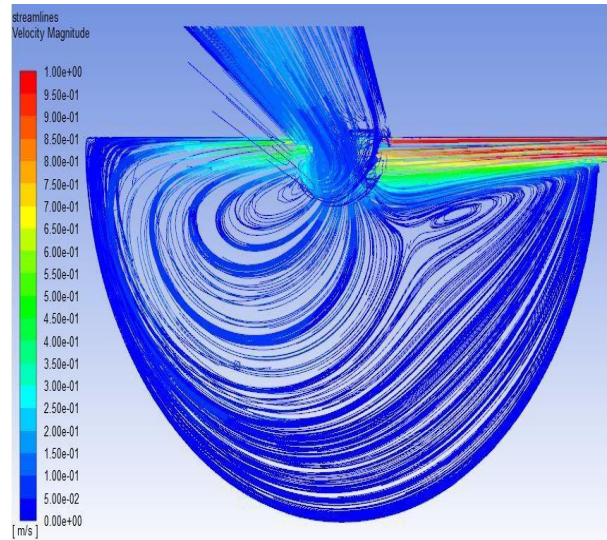
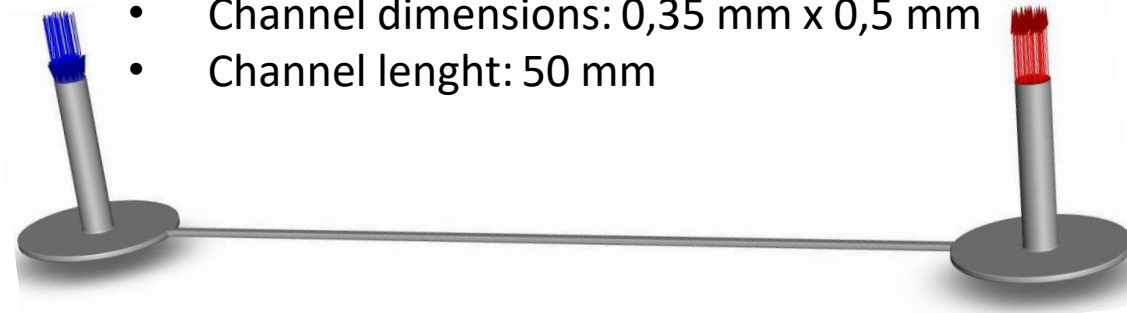
Objective of the simulation: Flow behavior of the liquid within the channel structure

Schematic:

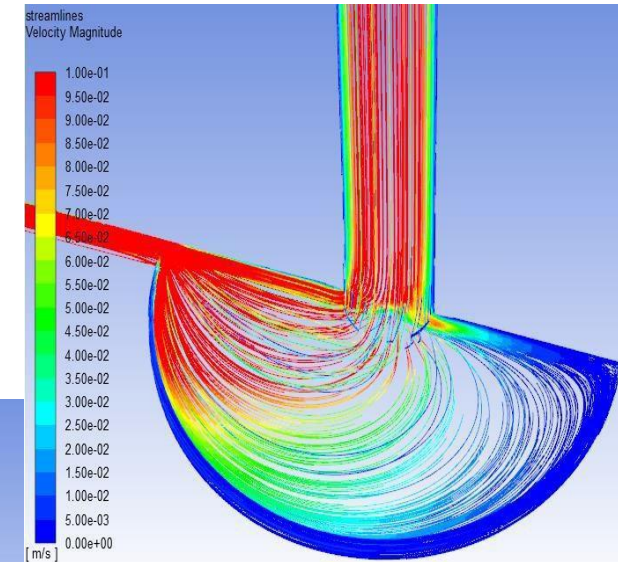


Fluidic configuration:

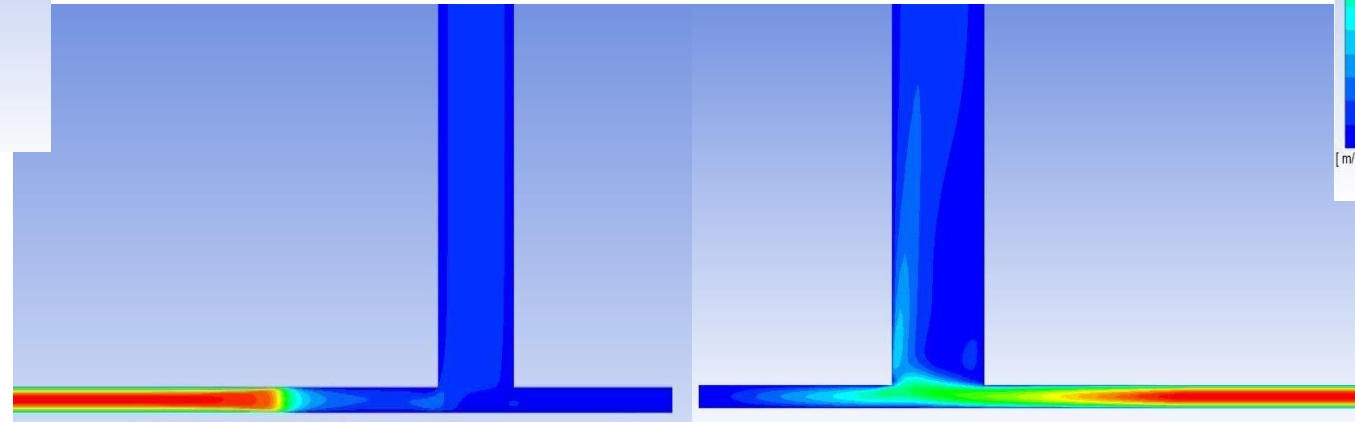
- Entrance/exit chamber: \varnothing 8mm
- Channel dimensions: 0,35 mm x 0,5 mm
- Channel length: 50 mm



Flow simulation entrance



Flow simulation exit



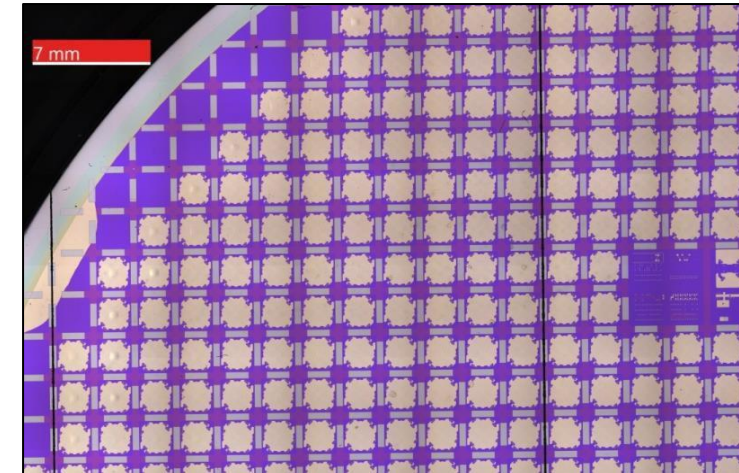
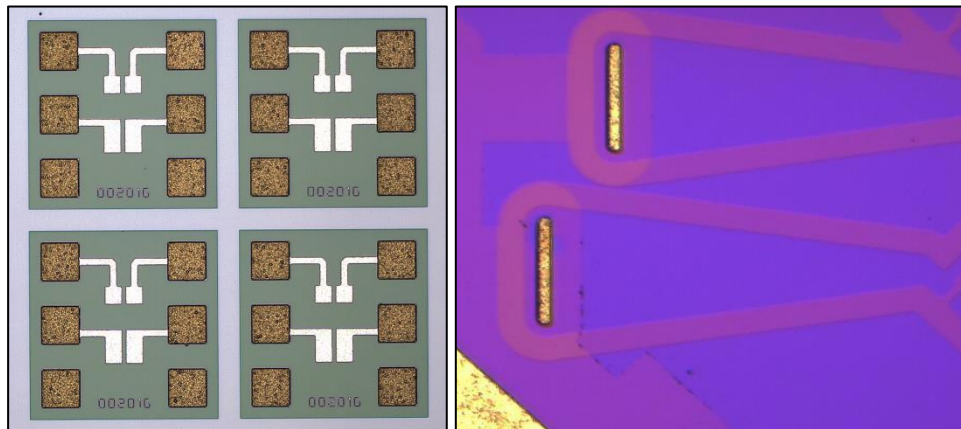
Velocity profile entrance

Velocity profile exit

Process development together with TU Imenau

- Evaluation of refiring under pressure
- Evaluation of relaxation structures during pressure sintering
- Development and transfer to wafer level process with BCT ceramic
- SAM-Analysis + optical analysis:

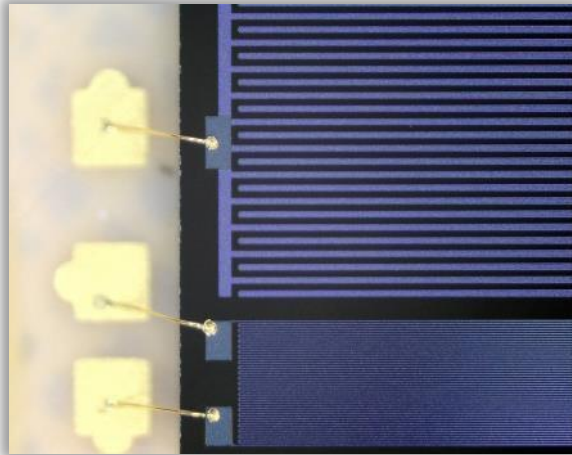
→ SiCer composit substrate without visible cracks and displacements



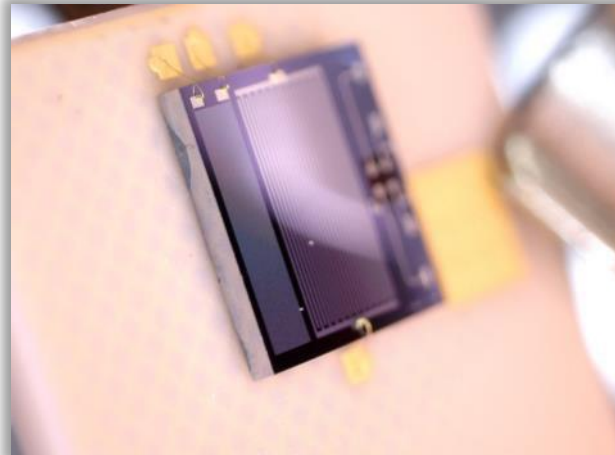
Wet chemical metallisation

- Test of maskless UBM
- Successful soldering on UBM (SAC)
- UBM compatible for geeignet für Flip-Chip-soldering
- Test of electrochemical metal deposition in the contact hole ongoing

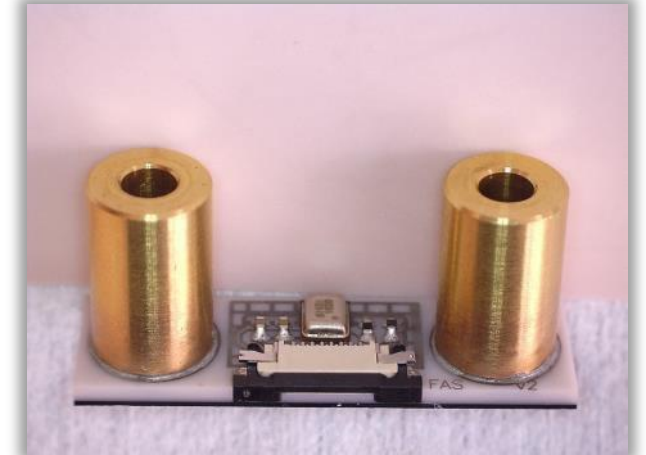
Reliable and established interconnection technologies on SiCer Substrates



Au wire bond between Si and ceramic side

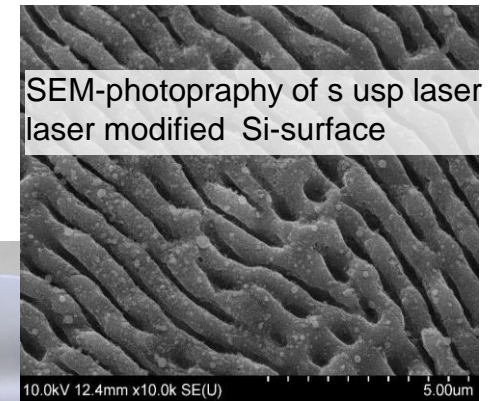


Assembly of a Si Chip onto the ceramic side by adhesive bonding

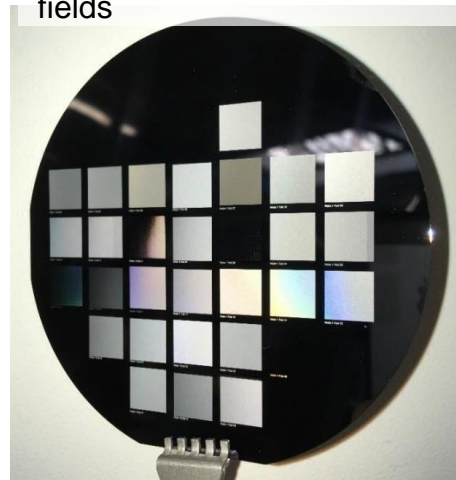


Soldered connectors and SMD components on SiCer

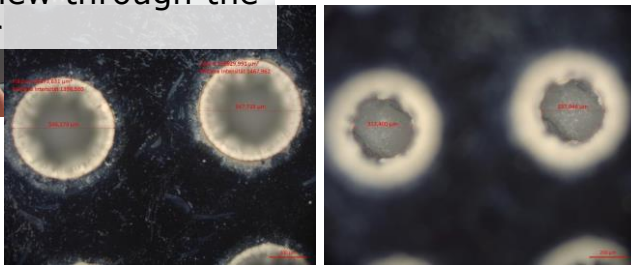
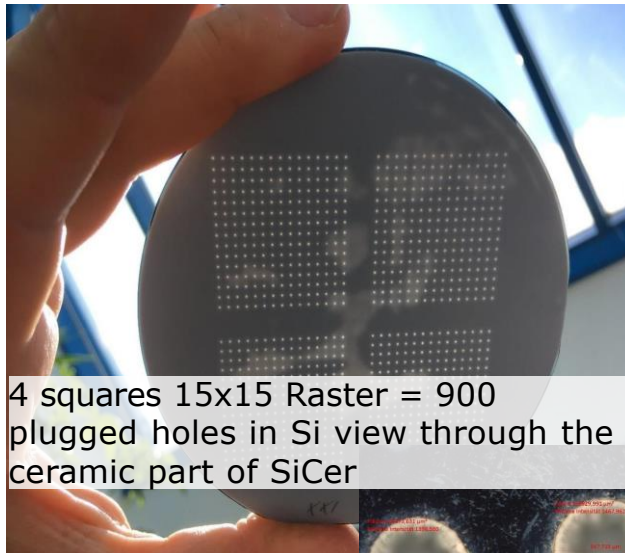
- **Plugged holes exactly adjusted to the depth of the Si on SiCer substrate** ending at the ceramic surface to provide TSVs.)
 - Test drills in Si for metallisation tests (100, 150, 200 und 300µm) realised
 - Testwafer with plugged holes ending at ceramic part of the SiCer substrate realised



4" Wafer with 30 parameter fields



- **Microstructures** of Si-Wafers to activate the surface and enhance the bond interface between Si and ceramic



3. Functionality and upscaling

- Structural and functional demonstrator elements in both LTCC and Si can be integrated
- USP laser processes for structural elements are developed and validated
- Cost efficient Ag-based metal paste for cofiring is developed and under evaluation
- TSV are developed and in verification
- Functional materials for SiCer integration are developed and under evaluation
- 2. generation tape material is developed and in evaluation
- Upscaling of the LTCC format from 4 to 6 Zoll is validated
- Upscaling of tape casting from batch casting to continuous casting is validated

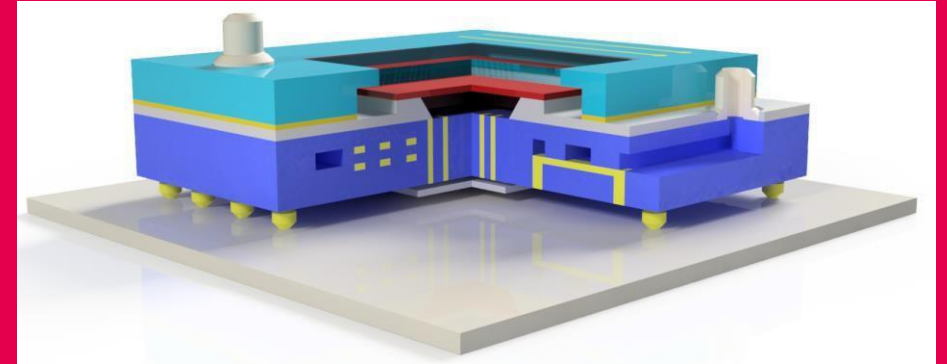
Integrated structures and functions as well as first sensor elements are realised based on the SiCer technology platform

The SiCer technology platform developed in the HIPS project offers mass production at highest performance

- **It Provides a maximum of integration density, complexity and functionality**
 - A thin film compatible Si side
 - Smallest MEMS und NEMS with integrated fluidic and functional elements
 - High resolution wiring
 - A thick film compatible ceramic side
 - Established interconnection technology and shortest signal lines from the sensor to the electronics
- **It performs with high reliability under extreme environmental conditions**
 - Cofire bond process up to 940°C and postfire process stability up to 600°C is justified
 - Matching of the TCE between LTCC und Si is verified

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Thanks to the partners and to the VIA team contributing to the work, thank you for your attention.